WHAT IS CLAIMED IS:

1. A photomask blank comprising:

a light-transmitting substrate; and

a shading layer part disposed on the light-transmitting substrate, the shading layer part comprising a first shading layer having a first hardness and a second shading layer having a second hardness,

wherein the first shading layer is disposed closer to the light-transmitting substrate than the second shading layer, and

a value of the first hardness is larger than a value of the second hardness, wherein the second hardness is 0.15 times to 0.55 times of the first hardness.

2. The photomask blank of claim 1,

wherein the second hardness is 0.3 kPa to 0.55 kPa.

3. The photomask blank of claim 1,

wherein a Young's modulus of the second shading layer is 1.0 kPa or more.

4. The photomask blank of claim 1,

wherein a value of standard deviation of adhesion forces of the second shading layer is measured at sixteen positions different from one another, which is 8 % or less of an average of the adhesion forces.

5. The photomask blank of claim 1,

wherein a value of standard deviation of pull off forces of the second shading layer is measured at sixteen positions different from one another, which is 5 % or less of an average of the pull off forces.

6. The photomask blank of claim 1,

wherein a second Young's modulus of the second shading layer is 0.15 times to 0.55 times of a first Young's modulus of the first shading layer.

7. The photomask blank of claim 1,

wherein a Young's modulus of the second shading layer is 1.0 kPa to 4.2 kPa.

8. The photomask blank of claim 1,

wherein a thickness of the second shading layer is 30 nm or more.

9. The photomask blank of claim 1,

wherein a thickness ratio of the first shading layer and a thickness ratio of the second shading layer is 1: 0.02 to 0.25.

10. The photomask blank of claim 1,

wherein a transmissivity of the shading layer part is 1 or more for light having a wavelength of 193 nm.

11. The photomask blank of claim 1,

wherein an optical density of the shading layer part is 1.8 or more for light having a wavelength of 193 nm.

12. A photomask blank comprising:

a light-transmitting substrate; and

a patterned shading layer part disposed on the light-transmitting substrate, the patterned shading layer part comprising a patterned first shading layer having a first Young's modulus and a patterned second shading layer having a second Young's modulus smaller than the first Young's modulus, wherein the second Young's modulus is 0.15 times to 0.55 times of the first Young's modulus,

wherein the patterned first shading layer is disposed closer to the light-transmitting substrate than the patterned second shading layer.

13. A manufacturing method of a semiconductor element comprising:

preparing a target substrate; and

applying a photomask on one surface of the target substrate to pattern the target substrate to form a patterned target substrate into a semiconductor element,

wherein the photomask comprises a patterned shading layer part disposed on a light-transmitting substrate, the patterned shading layer part comprising a patterned first shading layer having a first Young's modulus and a patterned second shading layer having a second Young's modulus smaller than the first Young's modulus, wherein the second Young's modulus is 0.15 times to 0.55 times of the first Young's modulus, and

wherein the patterned first shading layer is disposed closer to the light-transmitting substrate than the patterned second shading layer.